



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HEP31 Series

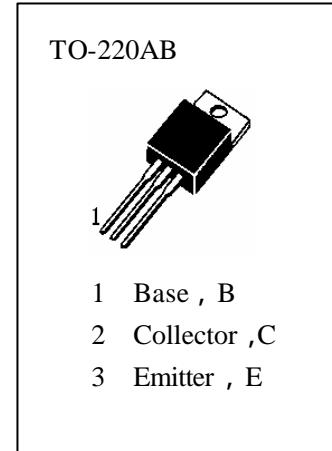
(HEP31/HEP31A/HEP31B/HEP31C)

APPLICATIONS

Medium Power Linear switching Applications.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation($T_c=25^\circ C$).....	40W
P_c —Collector Dissipation($T_a=25^\circ C$)	2W
V_{CBO} —Collector-Base Voltage、 V_{CEO} —Collector-Emitter Voltage HEP31.....	40V
HEP31A.....	60V
HEP31B.....	80V
HEP31C.....	100V
V_{EBO} —Emitter-Base Voltage.....	5V
I_c —Collector Current (DC)	3A
I_c —Collector Current (Pulse)	5A
I_b —Base Current.....	1A



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage HEP31	40			V	$I_c=30mA, I_B=0$
	HEP31A	60			V	
	HEP31B	80			V	
	HEP31C	100			V	
ICEO	Collector Cut-off Current HEP31/ HEP31A		0.3	mA		$V_{CB}=30V, I_B=0$
	HEP31B/ HEP31C		0.3	mA		
ICES	Collector Cut-off Current HEP31		200	μA		$V_{CE}=40V, V_{EB}=0$
	HEP31A		200	μA		
	HEP31B		200	μA		
	HEP31C		200	μA		
HFE (1)	*DC Current Gain	25				$V_{CE}=4V, I_C=1A$
HFE (2)		10	50			$V_{CE}=4V, I_C=3A$
VCE(sat)	*Collector- Emitter Saturation Voltage		1.2	V		$I_C=3A, I_B=375mA$
VBE(ON)	*Base-Emitter On Voltage		1.8	V		$V_{CE}=4V, I_C=3A$
IEBO	Emitter Cut-off Current		1	mA		$V_{EB}=5V, I_C=0$
fr	Current Gain-Bandwidth Product	3.0			MHz	$V_{CE}=10V, I_C=500mA, f=1MHz$

*Pulse Test : PW 300 μs , Duty cycle 2%



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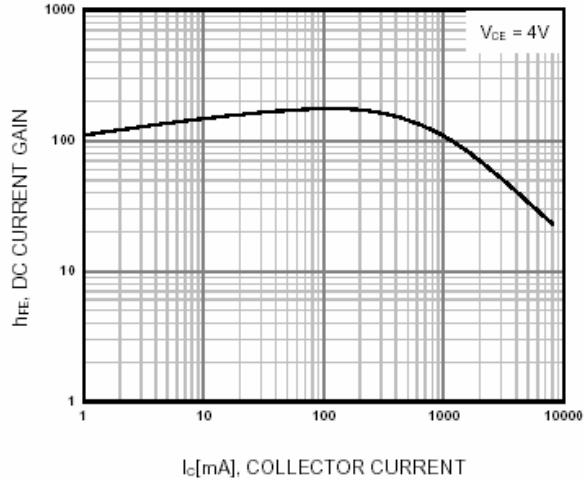


Figure 1. DC current Gain
 I_c [mA], COLLECTOR CURRENT

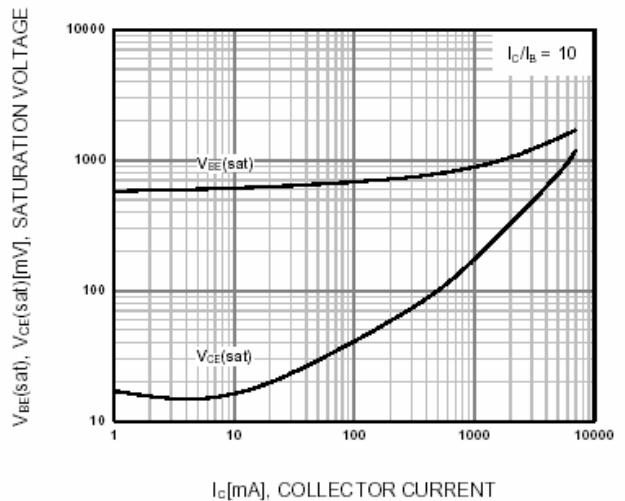


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage
 I_c [mA], COLLECTOR CURRENT

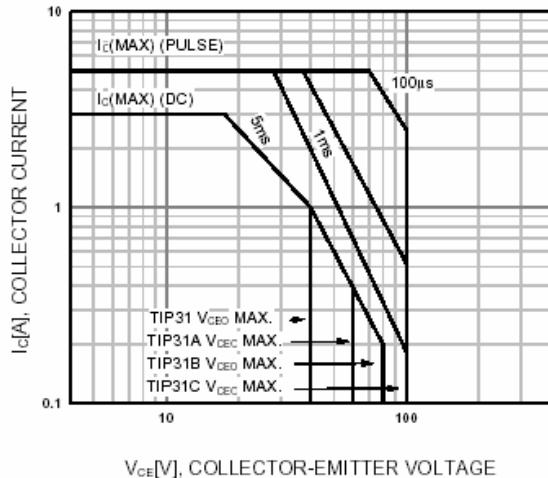


Figure 3. Safe Operating Area
 V_{CE} [V], COLLECTOR-EMITTER VOLTAGE

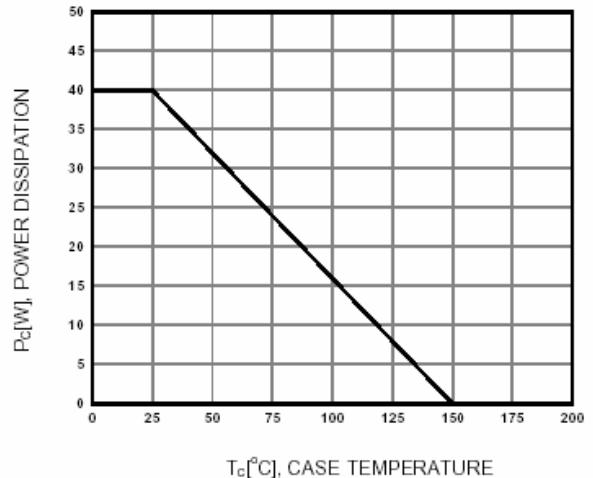


Figure 4. Power Derating
 T_c [°C], CASE TEMPERATURE